

TECHNICAL DATA
DATA SHEET 4077, REV. H

HERMETIC SILICON CARBIDE RECTIFIER

DESCRIPTION: A 600-VOLT, 20 AMP POWER SILICON CARBIDE RECTIFIER IN A CERAMIC HERMETIC SMD-0.5 PACKAGE

FEATURES:

- NO RECOVERY TIME OR REVERSE RECOVERY LOSSES
- NO TEMPERATURE INFLUENCE ON SWITCHING BEHAVIOR
- AVAILABLE SCREENED TO ANY REQUIRED LEVEL
- ADD SUFFIX "L" FOR RIBBON TERMINALS, (ie.SHD620051PL)

MAXIMUM RATINGS

ALL RATINGS ARE @ $T_C = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED.

RATING	SYMBOL	MAX.	UNITS
PEAK INVERSE VOLTAGE	PIV	600	Volts
MAXIMUM DC OUTPUT CURRENT (With $T_C = 65^\circ\text{C}$ for P suffix)	I_o	20	Amps
MAXIMUM DC OUTPUT CURRENT (With $T_C = 65^\circ\text{C}$ for Single)	I_o	10	Amps
MAXIMUM REPETITIVE FORWARD SURGE CURRENT PER LEG ($t = 8.3\text{ms}$, Sine) per leg, $T_C = 25^\circ\text{C}$	I_{FRM}	50	Amps
MAXIMUM POWER DISSIPATION, $T_C = 25^\circ\text{C}$ (SMD-0.5 package)	P_d	34	W
MAXIMUM THERMAL RESISTANCE, Junction to Case PER LEG (SMD-0.5 package)	$R_{\theta JC}$	4.4	$^\circ\text{C/W}$
MAXIMUM THERMAL RESISTANCE, Junction to Case PER LEG (SMD-0.5L package, measured to the end of the leads)	$R_{\theta JC}$	36	$^\circ\text{C/W}$
MAXIMUM OPERATING AND STORAGE TEMPERATURE RANGE*	Top, Tstg	-55 to 175	$^\circ\text{C}$

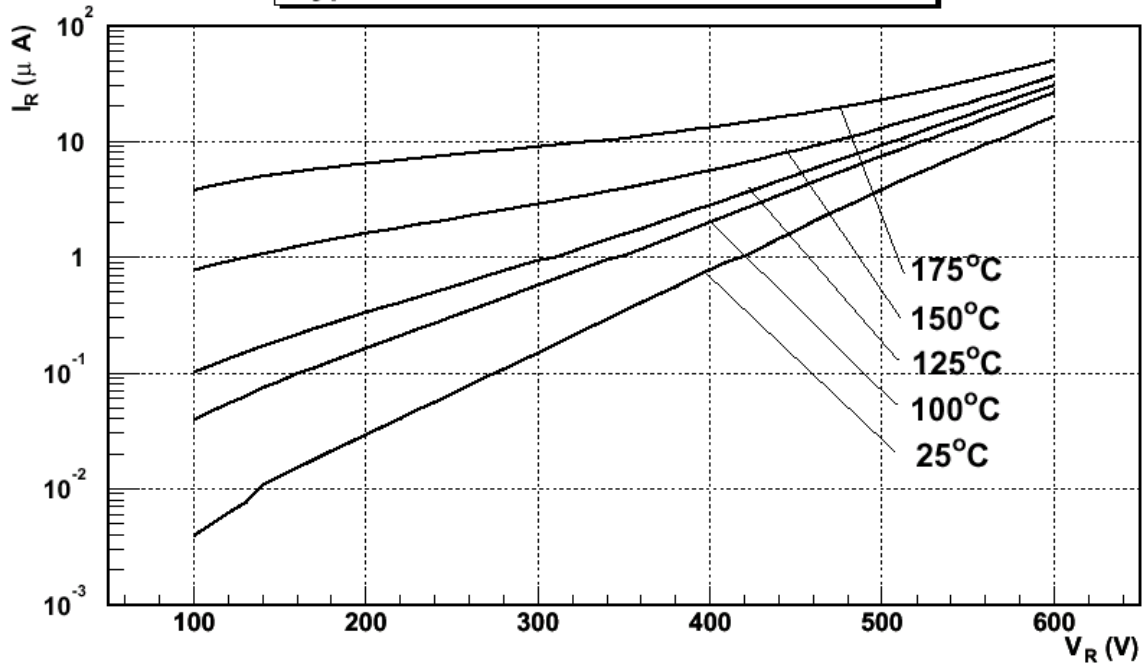
* Note: SiC semiconductors will handle at or above this operating and storage temperature. However, extended operational use of the packaged device above 175C may reduce its future performance. All qualification testing and screening per MIL-PRF-19500 will only be performed to 175C.

ELECTRICAL CHARACTERISTICS

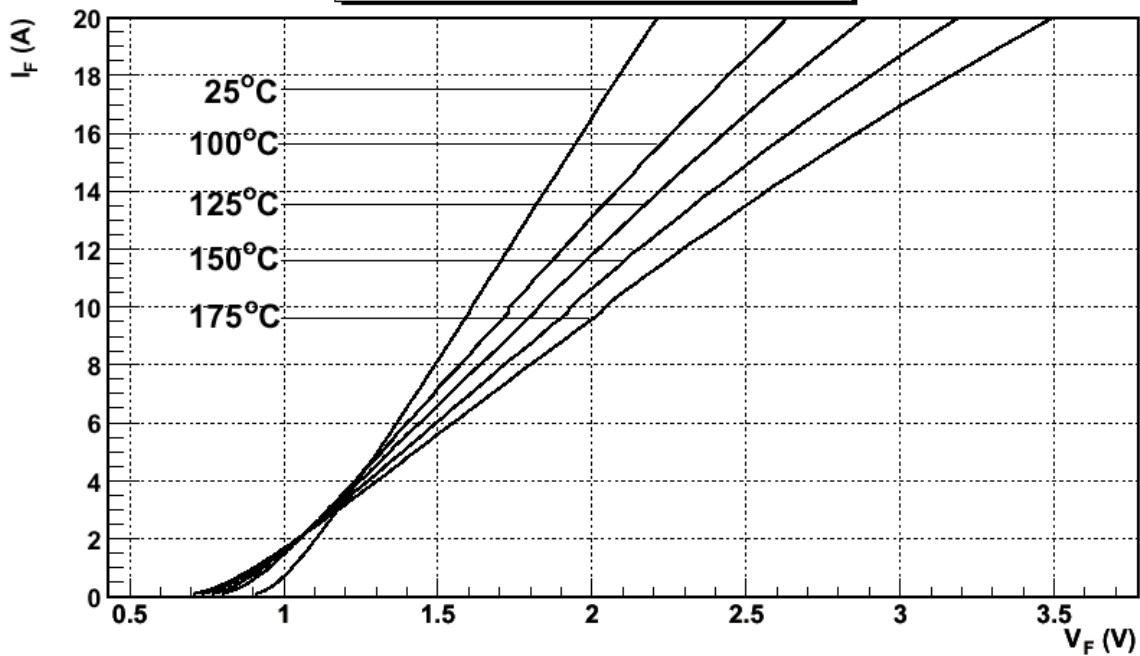
CHARACTERISTIC	TYP	MAX.	UNITS
MAXIMUM FORWARD VOLTAGE DROP Pulsed ($I_f = 10\text{ A PER LEG}$) V_f	$T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$	1.65 2.05	1.80 2.20 Volts
MAXIMUM FORWARD VOLTAGE DROP Pulsed ($I_f = 6\text{ A PER LEG}$) V_f	$T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$	1.35 1.60	1.45 1.70 Volts
MAXIMUM REVERSE CURRENT (I_r @ 600V PIV PER LEG)	$T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$	0.04 0.08	0.15 0.50 mA
JUNCTION CAPACITANCE C_T ($V_r = 5\text{V}$) per leg	C_T	250	350 pF
TOTAL CAPACITIVE CHARGE ($V_R = 600\text{V}$ $I_F = 20\text{A}$ $di/dt = 500\text{A}/\mu\text{s}$ $T_J = 25^\circ\text{C}$) This is design information only	Q_c per leg	35	N/A nC

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DATA SHEET 4077, REV. H

Typical Reverse Current Characteristics



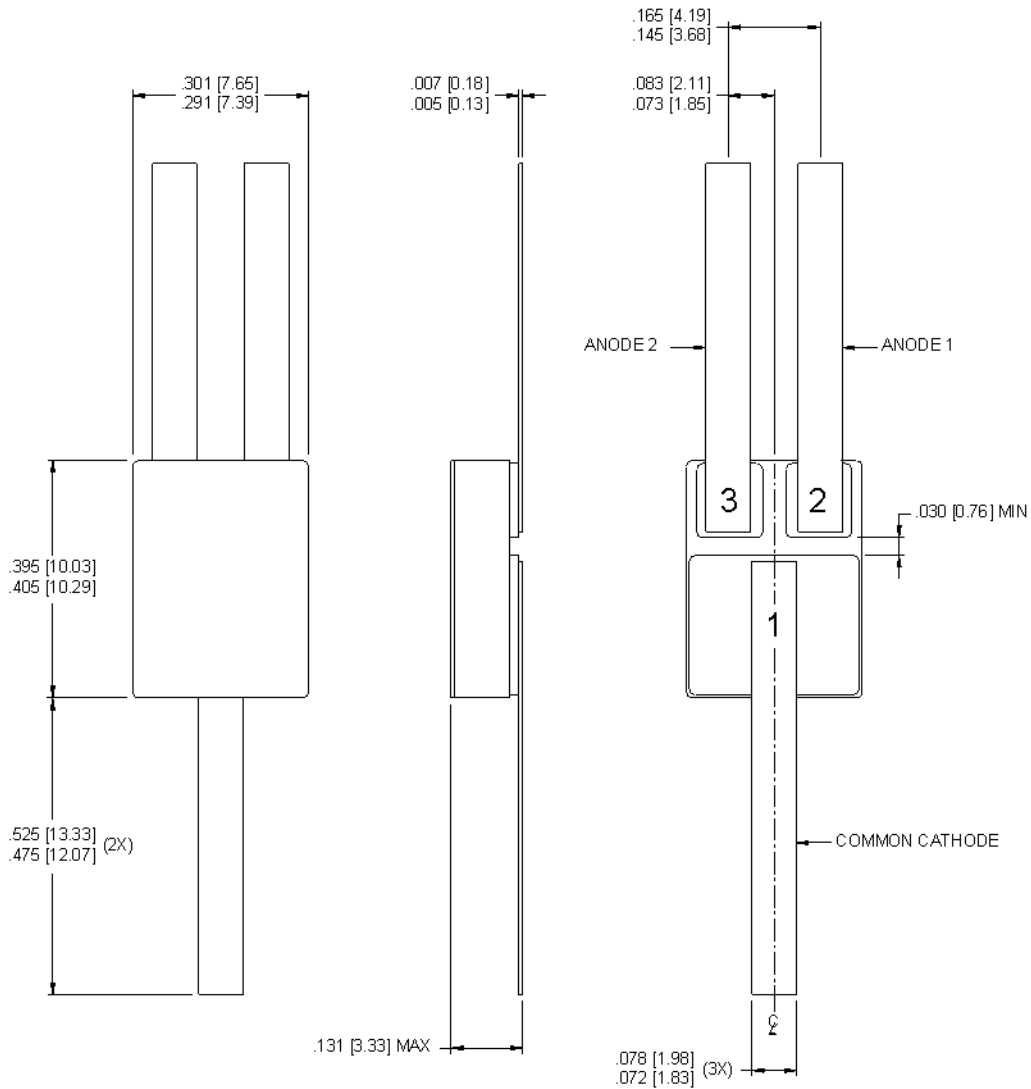
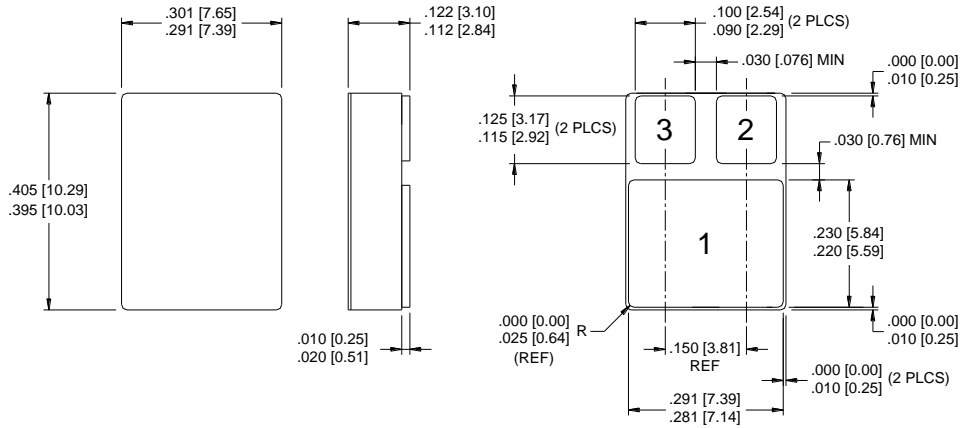
Typical Forward Characteristics



TECHNICAL DATA
DATA SHEET 4077, REV. H

MECHANICAL DIMENSIONS: inches / mm

SMD-0.5

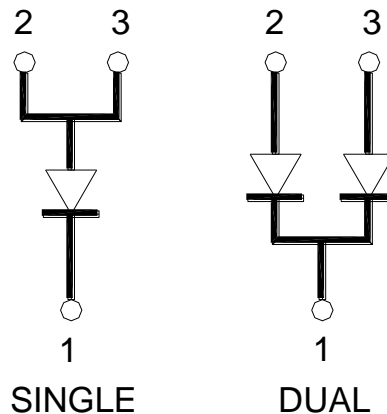


SMD-0.5L

SENSITRON
SEMICONDUCTOR

SHD620051
SHD620051P

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PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P) (PL)	COMMON CATHODE	ANODE 1	ANODE 2

Application Note: Customers should be aware that at the current stage of technical development of SiC, the reverse avalanche capabilities of the device are limited.

Customer designs will need to accommodate these limitations and avoid exposure of the device to this and other potentially damaging conditions in their applications.

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